

2N681,A THRU 2N692,A

SILICON CONTROLLED RECTIFIER
25 AMPS, 25 THRU 800 VOLTS

JEDEC TO-48 CASE

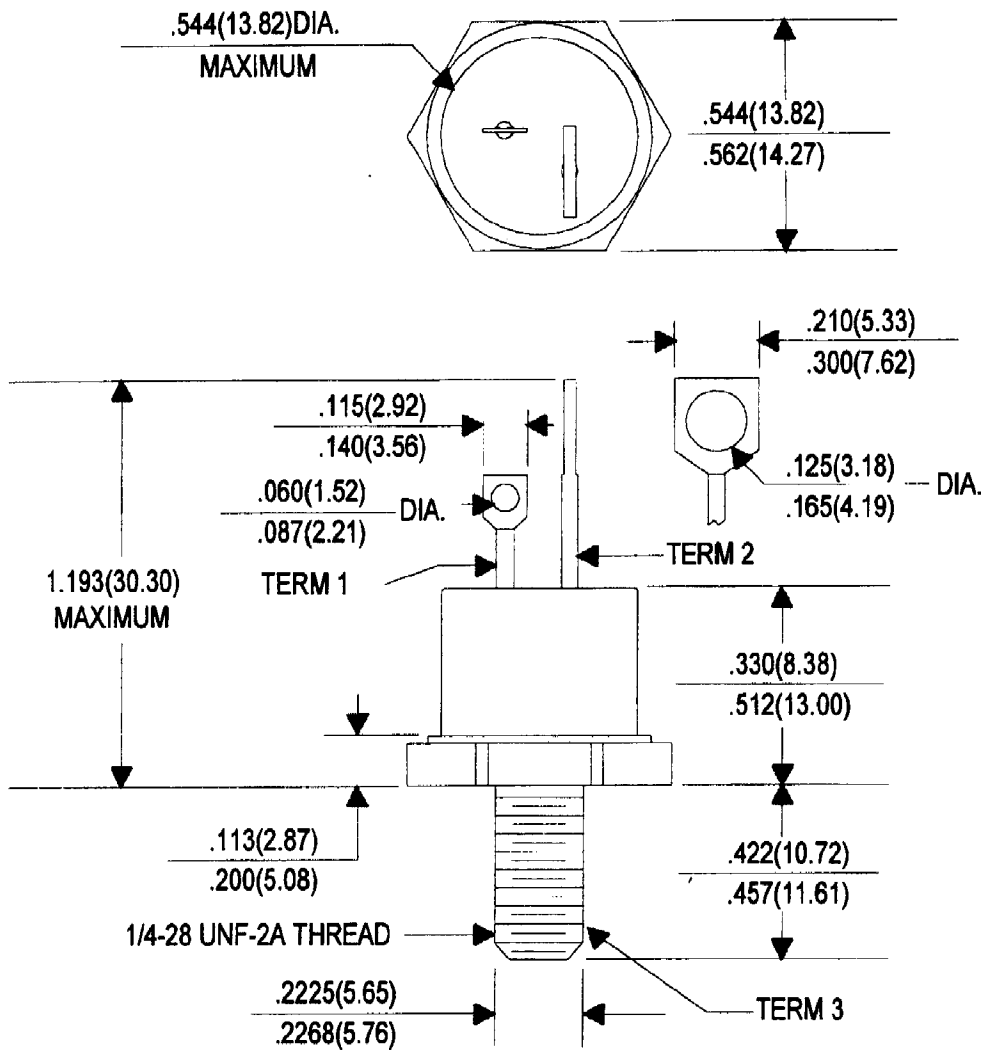
MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

	2N6 81.A	2N6 82.A	2N6 83.A	2N6 84.A	2N6 85.A	2N6 86.A	2N6 87.A	2N6 88.A	2N6 89.A	2N6 90.A	2N6 91.A	2N6 92.A	UNITS
V_{DRM}	25	50	100	150	200	250	300	400	500	600	700	800	V
V_{RRM}	25	50	100	150	200	250	300	400	500	600	700	800	V
V_{RSM}	25	50	100	150	200	250	300	400	500	600	700	800	V
RMS On-State Current ($T_C=70^\circ\text{C}$)							$I_T(\text{RMS})$	25					A
Peak One Cycle Surge Current (60Hz)							I_{TSM}	200					A
Peak Gate Power Dissipation							P_{GM}	5.0					W
Average Gate Power Dissipation							$P_{G(AV)}$	0.5					W
Storage Temperature							T_{stg}	-65 to +150					$^\circ\text{C}$
Operating Junction Temperature							T_J	-65 to +125					$^\circ\text{C}$
Thermal Resistance, Junction to Case							θ_{JC}	1.5					$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N681,A, 2N682, 2N683, 2N684,A)			13	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N685,A)			12	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N686,A)			11	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N687,A)			10	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N688,A)			8.0	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N689,A)			6.0	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N690,A)			5.0	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N691,A)			4.5	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N692,A)			4.0	mA
I_{GT}	$V_D=12\text{V}, R_L=50\Omega$			40	mA
V_{GT}	$V_D=12\text{V}, R_L=50\Omega$			2.0	V
V_{TM}	$I_{TM}=50\text{A}, \text{PW}=1.0\text{ms}, \text{D.C}=2.0\%$			2.0	V
I_H	$V_D=7.0\text{V}, R_{GK}=1\text{K}\Omega$ (2N681 thru 2N692)			100	mA
I_H	$V_D=7.0\text{V}, R_{GK}=1\text{K}\Omega$ (2N681A thru 2N692A)			50	mA
dv/dt	Rated $V_{DRM}, T_C=125^\circ\text{C}$		100		V/ μs
t_{on}	$I_F=10\text{A}, I_G=200\text{mA}$		2.0		μs
t_{off}	$I_F=10\text{A}, I_G=200\text{mA}$		15		μs





All Dimensions in Inches (mm).

LEAD CODE:

TERM 1) GATE
 TERM 2) CATHODE
 TERM 3) ANODE